



ELECTRONICS, INC.
 44 FARRAND STREET
 BLOOMFIELD, NJ 07003
 (973) 748-5089

NTE6200 thru NTE6210 Positive Center Tapped Silicon Rectifiers 30 Amp(15A per diode)

Features:

- Available in Standard (NTE6200 & NTE6202) and Fast (NTE6206 thru NTE6210) Recovery
- 250 Amps Peak One Half Cycle Surge Current
- Fast Recovery Types: $t_{rr} = 200ns$ Max
- TO3 Type Package

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

DC Blocking Voltage, V_{RM}	
Working Peak Reverse Voltage, V_{DRM}	
Peak Repetitive Reverse Voltage, V_{RRM}	
NTE6200, NTE6206	200V
NTE6202, NTE6208	400V
NTE6210	600V
RMS Reverse Voltage, $V_{R(RMS)}$	
NTE6200, NTE6206	140V
NTE6202, NTE6208	280V
NTE6210	420V
Peak Surge Current (Per Diode, 1/2 Cycle at 60Hz, (Non-Repetitive), $T_C = +100^\circ C$), I_{FSM}	150A
Peak Surge Current (Per Diode, 1 sec at 60Hz, $T_C = +100^\circ C$), I_{FRM}	50A
Average Forward Current (Per Diode, $T_C = +100^\circ C$), I_O	15A
Fusing Data, I^2T	85A ² sec
Operating Junction Temperature Range, T_j	-65° to +150°C
Storage Temperature Range, T_{stg}	-65° to +150°C
Maximum Thermal Resistance, Junction-to-Case, R_{thJC}	1.5°C/W

Electrical Characteristics: ($T_A = +25^\circ C$ unless otherwise specified)

Maximum Instantaneous Forward Voltage Drop (Per Diode @ 15A), V_{FM}	1.4V
Maximum Reverse Current (At Rated V_{RM} , $T_C = +100^\circ C$), I_{RM}	5mA
Maximum Reverse Recovery Time ($I_F = 1A$, $I_A = 2A$), t_{rr}	200ns

